DATA SHEET
www.onsemi.com

100 V, 2.0 A, Low $V_{CE(sat)}$ PNP Transistor

NSS1C200L, NSV1C200L

onsemi’s e^2PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC–DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e^2PowerEdge devices to be driven directly from PMU’s control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

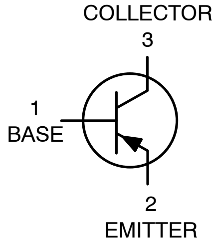
Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	–100	Vdc
Collector-Base Voltage	V_{CBO}	–140	Vdc
Emitter-Base Voltage	V_{EBO}	–7.0	Vdc
Collector Current – Continuous	I_C	–2.0	A
Collector Current – Peak	I_{CM}	–3.0	A

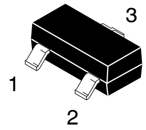
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D (Note 1)	490 3.7	mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$ (Note 1)	255	°C/W
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D (Note 2)	710 4.3	mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$ (Note 2)	176	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. FR–4 @ 100 mm^2, 1 oz. copper traces.
2. FR–4 @ 500 mm^2, 1 oz. copper traces.

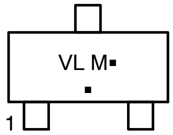
–100 VOLTS, 2.0 AMPS PNP LOW $V_{CE(sat)}$ TRANSISTOR





SOT–23 (TO–236)
CASE 318
STYLE 6

MARKING DIAGRAM



VL = Specific Device Code
M = Date Code*
▪ = Pb–Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping[†]
NSS1C200LT1G, NSV1C200LT1G	SOT–23 (Pb–Free)	3000/Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage (I_C = −10 mAdc, I_B = 0)	$V_{(BR)CEO}$	−100			Vdc
Collector−Base Breakdown Voltage (I_C = −0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	−140			Vdc
Emitter−Base Breakdown Voltage (I_E = −0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	−7.0			Vdc
Collector Cutoff Current (V_{CB} = −140 Vdc, I_E = 0)	I_{CBO}			−100	nAdc
Emitter Cutoff Current (V_{EB} = −6.0 Vdc)	I_{EBO}			−50	nAdc
ON CHARACTERISTICS					
DC Current Gain (Note 3) (I_C = −10 mA, V_{CE} = −2.0 V) (I_C = −500 mA, V_{CE} = −2.0 V) (I_C = −1.0 A, V_{CE} = −2.0 V) (I_C = −2.0 A, V_{CE} = −2.0 V)	h_{FE}	 150 120 80 50	 240	 360	
Collector−Emitter Saturation Voltage (Note 3) (I_C = −0.1 A, I_B = −0.01 A) (I_C = −0.5 A, I_B = −0.05 A) (I_C = −1.0 A, I_B = −0.100 A) (I_C = −2.0 A, I_B = −0.200 A)	$V_{CE(sat)}$			 −0.040 −0.080 −0.115 −0.250	V
Base−Emitter Saturation Voltage (Note 3) (I_C = −1.0 A, I_B = −0.100 A)	$V_{BE(sat)}$			−0.950	V
Base−Emitter Turn−on Voltage (Note 3) (I_C = −1.0 A, V_{CE} = −2.0 V)	$V_{BE(on)}$			−0.850	V
Cutoff Frequency (I_C = −100 mA, V_{CE} = −5.0 V, f = 100 MHz)	f_T		120		MHz
Input Capacitance (V_{EB} = 2.0 V, f = 1.0 MHz)	Cibo		200		pF
Output Capacitance (V_{CB} = 10 V, f = 1.0 MHz)	Cobo		22		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

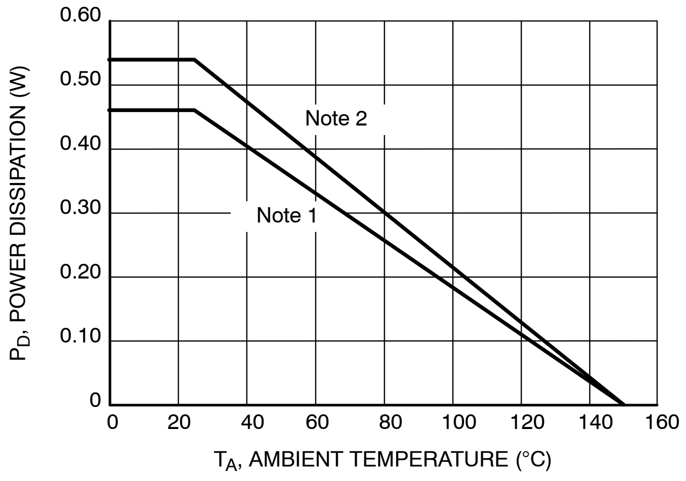


Figure 1. Power Derating

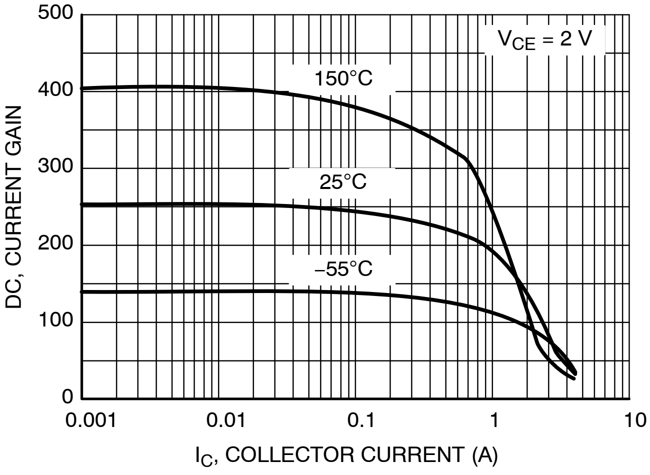


Figure 2. DC Current Gain

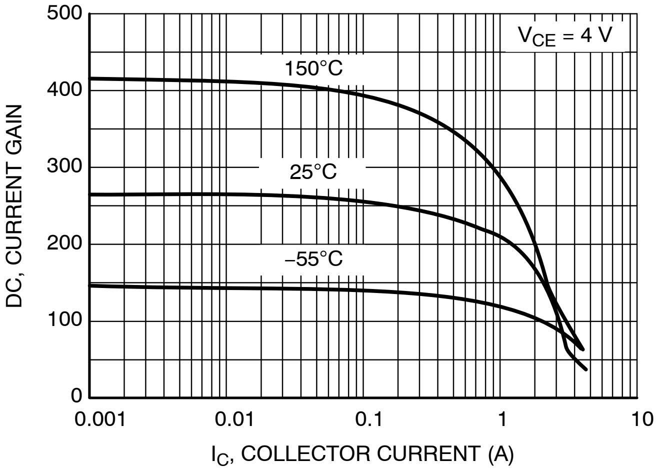


Figure 3. DC Current Gain

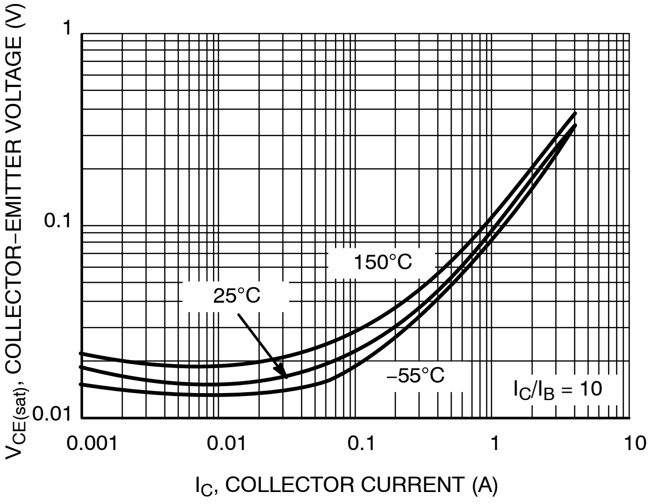


Figure 4. Collector−Emitter Saturation Voltage

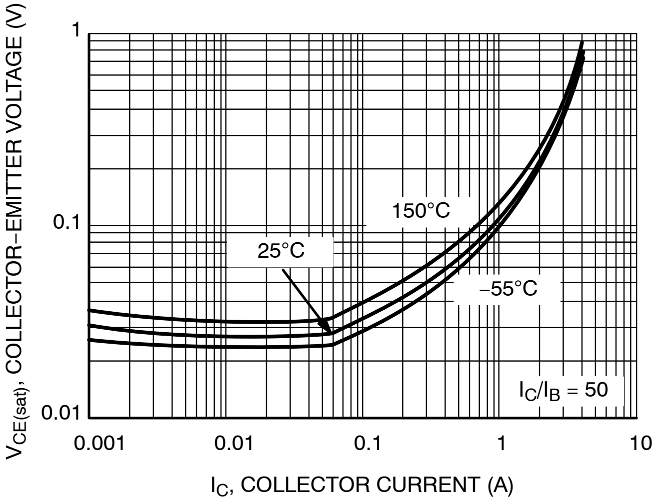


Figure 5. Collector−Emitter Saturation Voltage

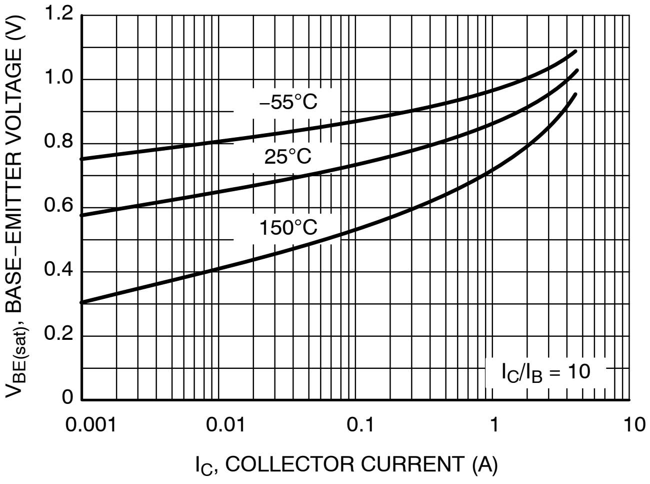


Figure 6. Base−Emitter Saturation Voltage

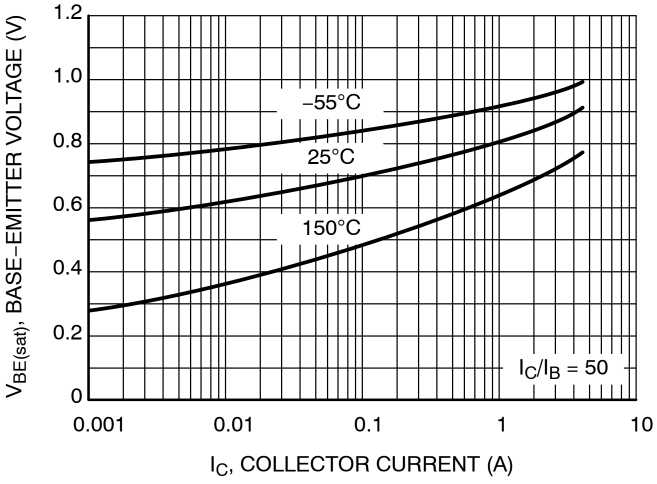


Figure 7. Base−Emitter Saturation Voltage

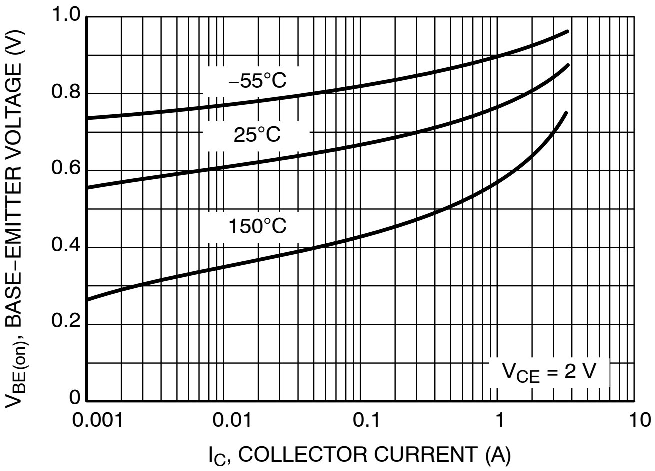


Figure 8. Base−Emitter Saturation Voltage

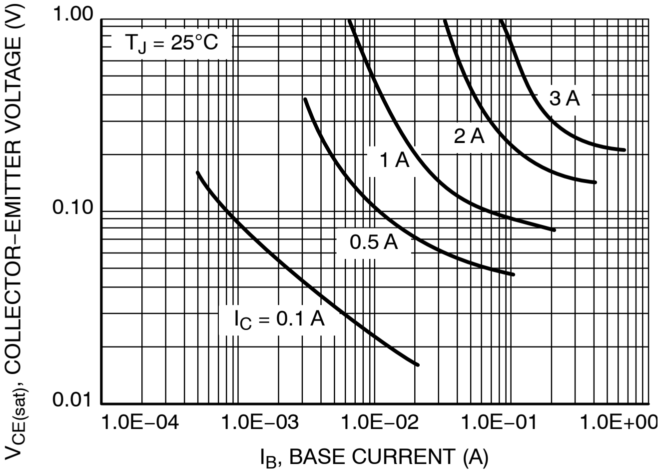


Figure 9. Collector Saturation Region

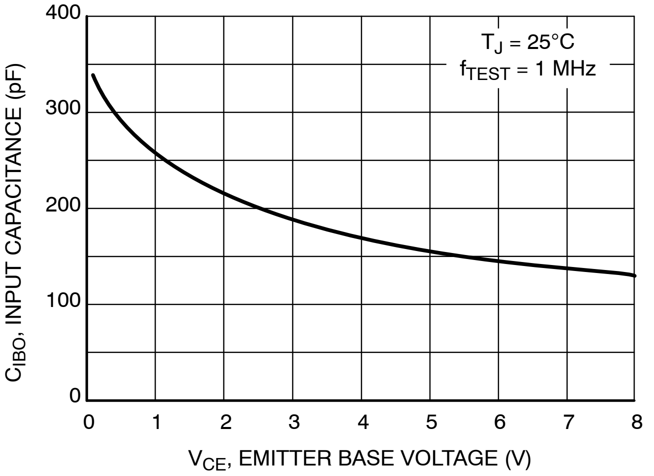


Figure 10. Input Capacitance

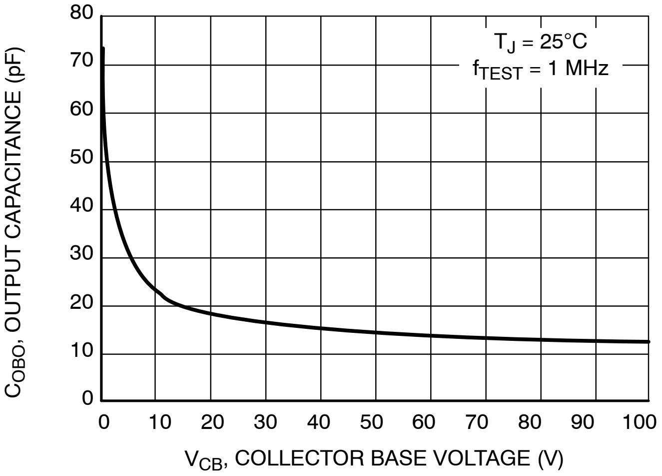


Figure 11. Output Capacitance

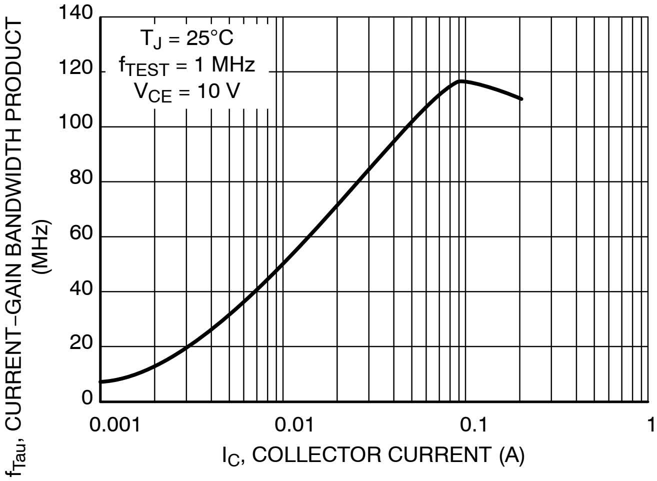


Figure 12. Current−Gain Bandwidth Product

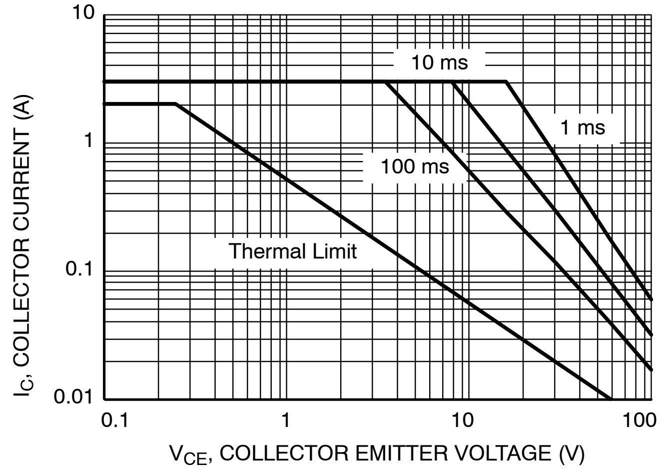


Figure 13.

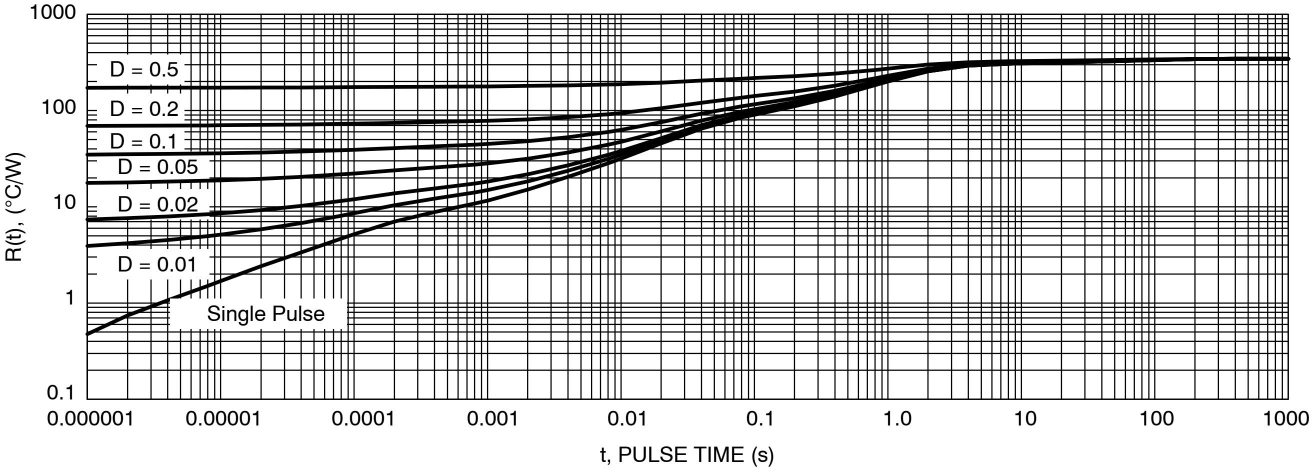
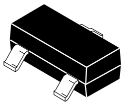


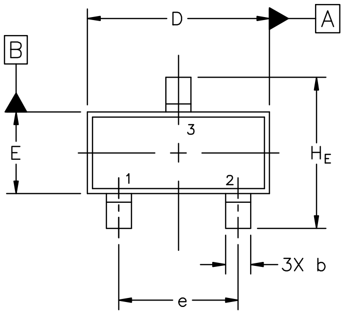
Figure 14. Transient Thermal Resistnce



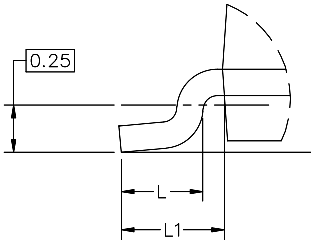
SCALE 4:1

SOT–23 (TO–236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

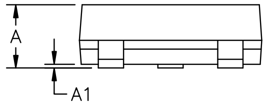


TOP VIEW

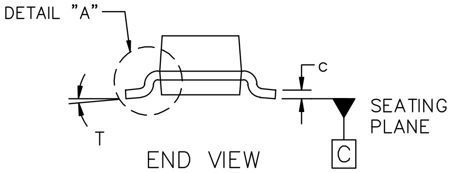


DETAIL ”A”
Scale 3:1

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	---	10°



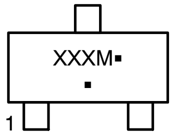
SIDE VIEW



END VIEW

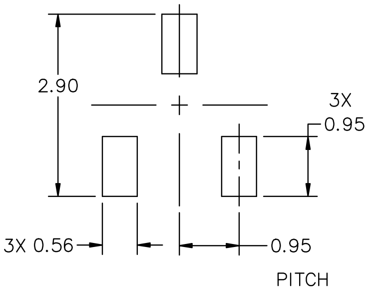
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb–Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb–Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
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DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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